

Vishay Siliconix

N-Channel 40 V (D-S) MOSFET

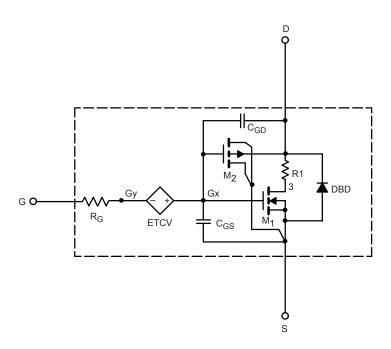
DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched $C_{\rm gd}$ model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- · Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics



Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

SPICE Device Model SiR418DP

Vishay Siliconix



SPECIFICATIONS T _J = 25 °C, unless otherwise noted					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.3	-	V
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	0.0041	0.0041	Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 15 \text{ A}$	0.0049	0.0048	
Forward Transconductancea	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$	76	95	S
Diode Forward Voltage ^a	V _{SD}	I _S = 4 A	0.71	0.71	V
Dynamic ^b					
Input Capacitance	C _{iss}	V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz	2390	2410	pF
Output Capacitance	C _{oss}		376	371	
Reverse Transfer Capacitance	C _{rss}		142	141	
Total Gate Charge	Qg	V _{DS} = 20 V, V _{GS} = 10 V, I _D = 20 A	37	50	nC
		V _{DS} = 20 V, V _{GS} = 4.5 V, I _D = 20 A	18	24	
Gate-Source Charge	Q _{gs}		6.5	6.5	
Gate-Drain Charge	Q_{gd}		7	7	

Notes

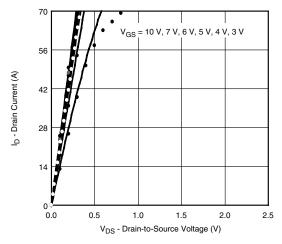
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

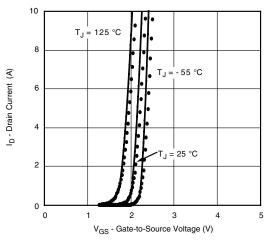
b. Guaranteed by design, not subject to production testing.

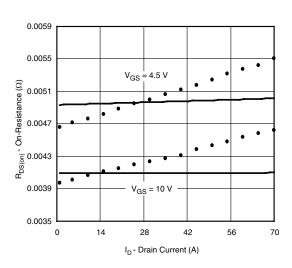


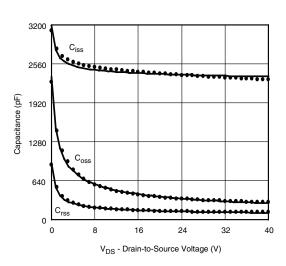
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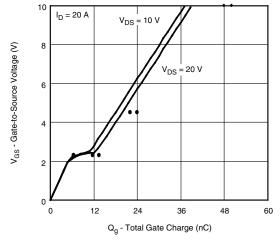
COMPARISON OF MODEL WITH MEASURED DATA $T_J = 25$ °C, unless otherwise noted

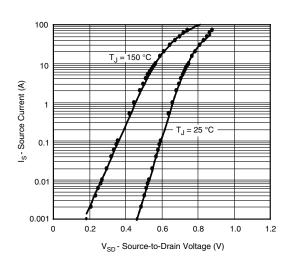












Note

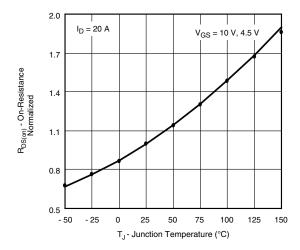
Dots and squares represent measured data.

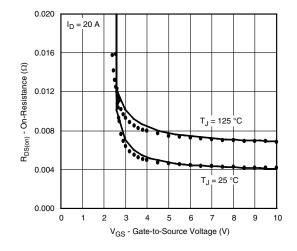
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COMPARISON OF MODEL WITH MEASURED DATA $T_J = 25~{}^{\circ}C$, unless otherwise noted





Note

Dots and squares represent measured data.



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